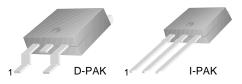


MJD122

D-PAK for Surface Mount Applications

- High DC Current Gain
- Built-in a Damper Diode at E-C
- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (I-PAK, " I " Suffix)
- Electrically Similar to Popular TIP122
- Complement to MJD127

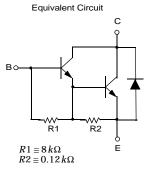


1.Base 2.Collector 3.Emitter

NPN Silicon Darlington Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	8	Α
I _{CP}	Collector Current (Pulse)	16	Α
I _B	Base Current	120	mA
P _C	Collector Dissipation (T _C =25°C)	20	W
	Collector Dissipation (T _a =25°C)	1.75	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C



Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustaining Voltage	$I_C = 30 \text{mA}, I_B = 0$	100		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = 50V, I_{B} = 0$		10	μΑ
I _{CBO}	Collector Cut-off Current	V _{CB} = 100V, I _E = 0		10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		2	mA
h _{FE}	*DC Current Gain	V _{CE} = 4V, I _C = 4A V _{CE} = 4V, V _{EB} = 8A	1000 100	12K	
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_C = 4A, I_B = 16mA$ $I_C = 8A, I_B = 80mA$		2 4	V V
V _{BE} (sat)	*Base-Emitter Saturation Voltage	$I_C = 8A, I_B = 80mA$		4.5	V
V _{BE} (on)	*Base-Emitter ON Voltage	$V_{CE} = 4V$, $I_{C} = 4A$		2.8	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0$ f= 0.1MHz		200	pF

^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

Typical Characteristics

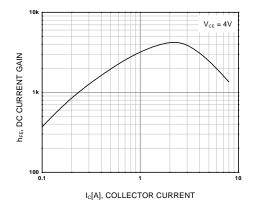


Figure 1. DC current Gain

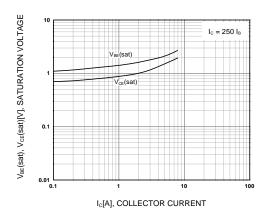


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

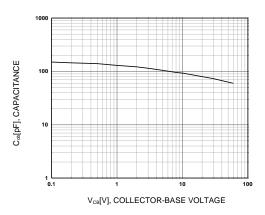


Figure 3. Collector Output Capacitance

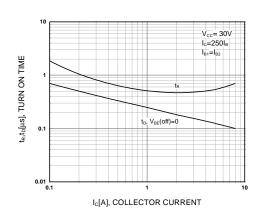


Figure 4. Turn On Time

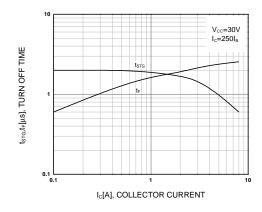


Figure 5. Turn Off Time

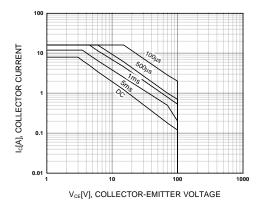


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

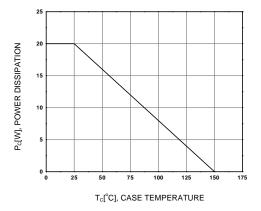
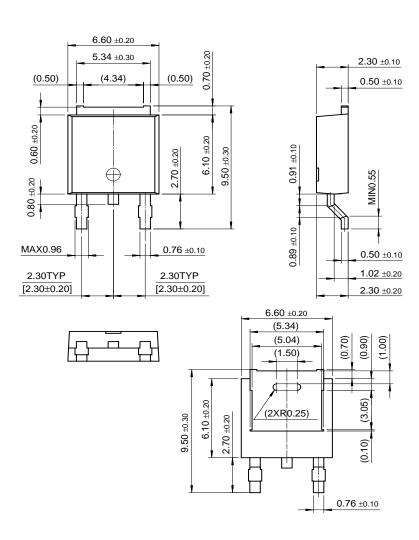


Figure 7. Power Derating

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Package Demensions

D-PAK



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